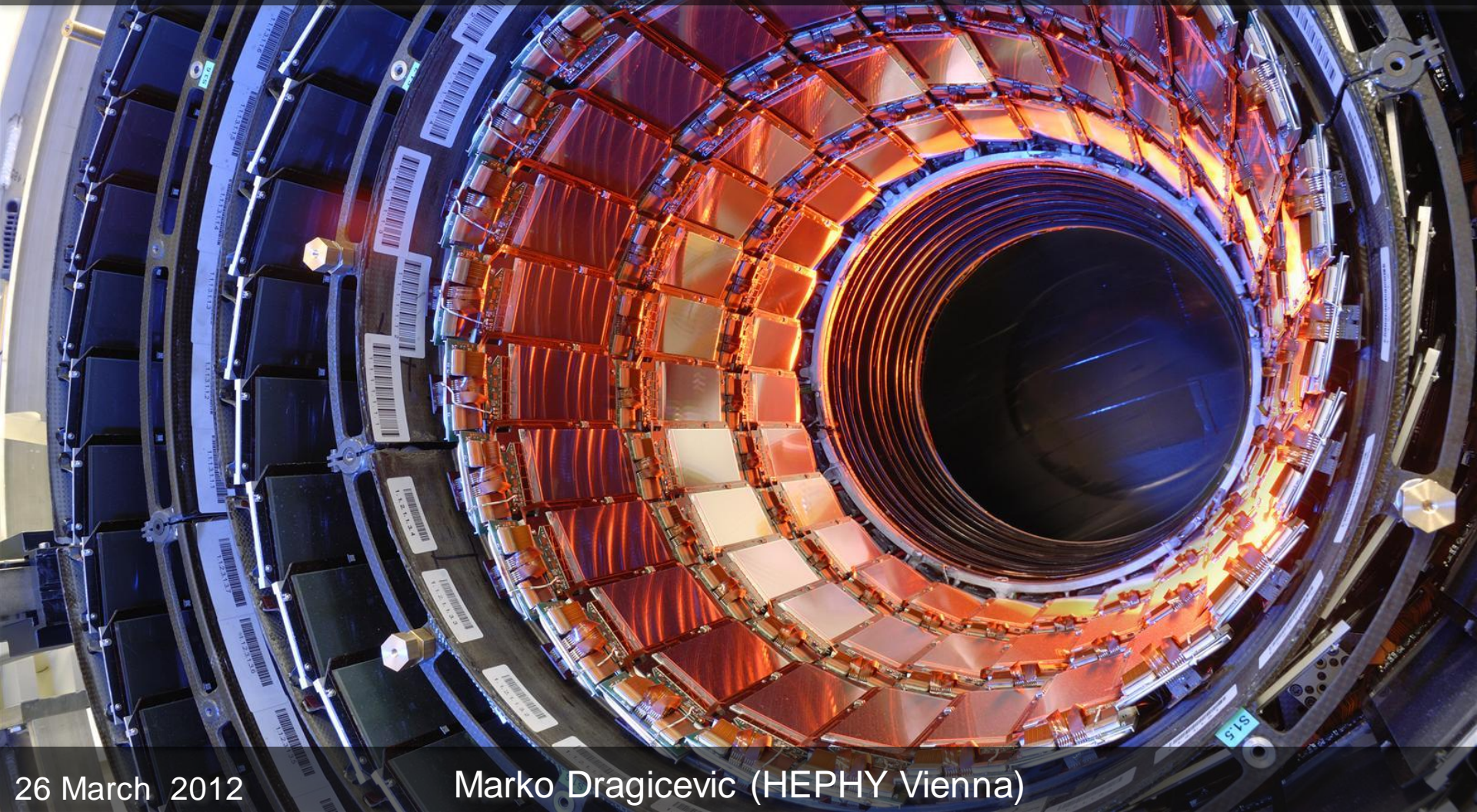


Needs of the CMS Strip Tracker

AIDA - Academia meets Industry Event



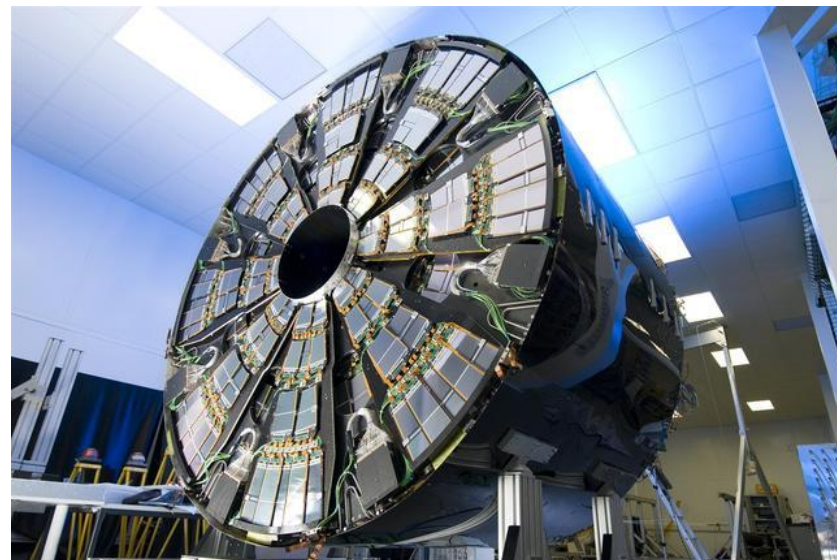
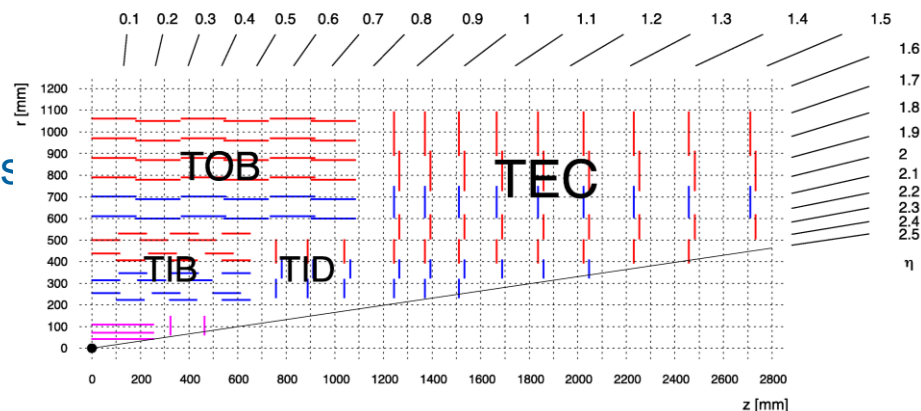
Current CMS Tracker

Tracker

- Barrel & Endcap geometry
- 200 m² of silicon
- 15.000 detector modules with 25.000 sensors
- Operating temperature < -10° C
- Expected fluence (10 years)
1x10¹⁴ 1 MeV Neutron/cm²

Sensors

- 6" wafers, high resistivity FZ <100>
 - 500 μm thickness: 3.5–7.5 kΩcm
 - 320 μm thickness: 1.5–3.0 kΩcm
- p-on-n processing
- AC coupled strips
- PolySilicon resistor biasing
- Strip length ~10 cm
- 15 different sensor geometries ≈ 10x10 cm² (rectangular and wedge shaped)

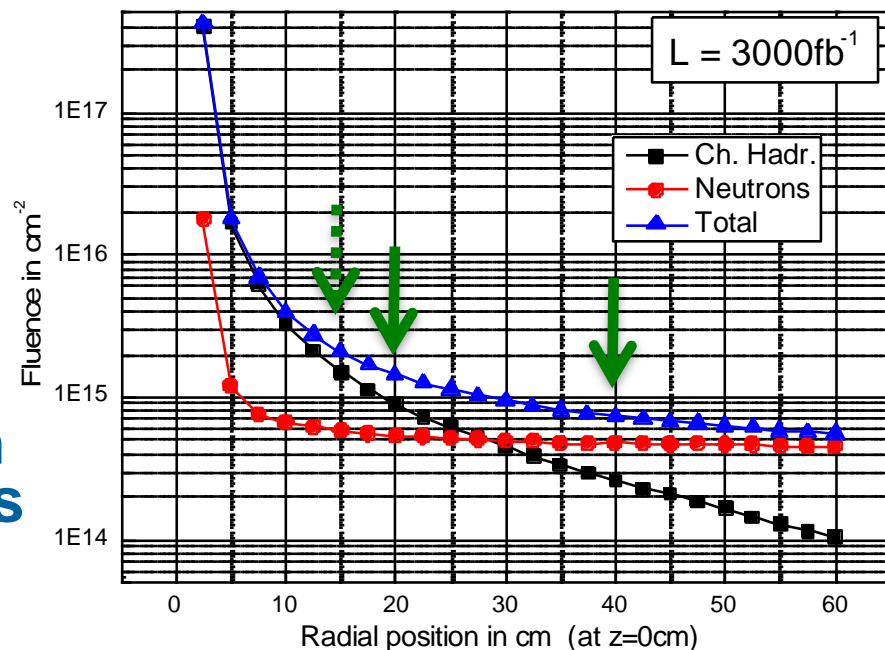


New CMS Tracker

- Performance of current tracker will have degraded significantly due to radiation damage by 2020
- Luminosity upgrade of the LHC
 - High-Luminosity-LHC = 5 x LHC
- Installation of the new tracker: **2020-2022**
- Two main challenges for the CMS Tracker
 - Even harsher radiation environment
 - Provide tracker information to the first level trigger

Challenges for the Upgrade: Radiation

- **Radiation dose** is about **5 – 10 times higher** than in current tracker
- Detector has to **survive 10 years** of operation
- Today's sensor technology might be sufficiently radiation tolerant for **outermost layers**
- For **intermediate to inner layers** we have a number of possible candidate materials/technologies
- *Innermost layers might even require something new?*

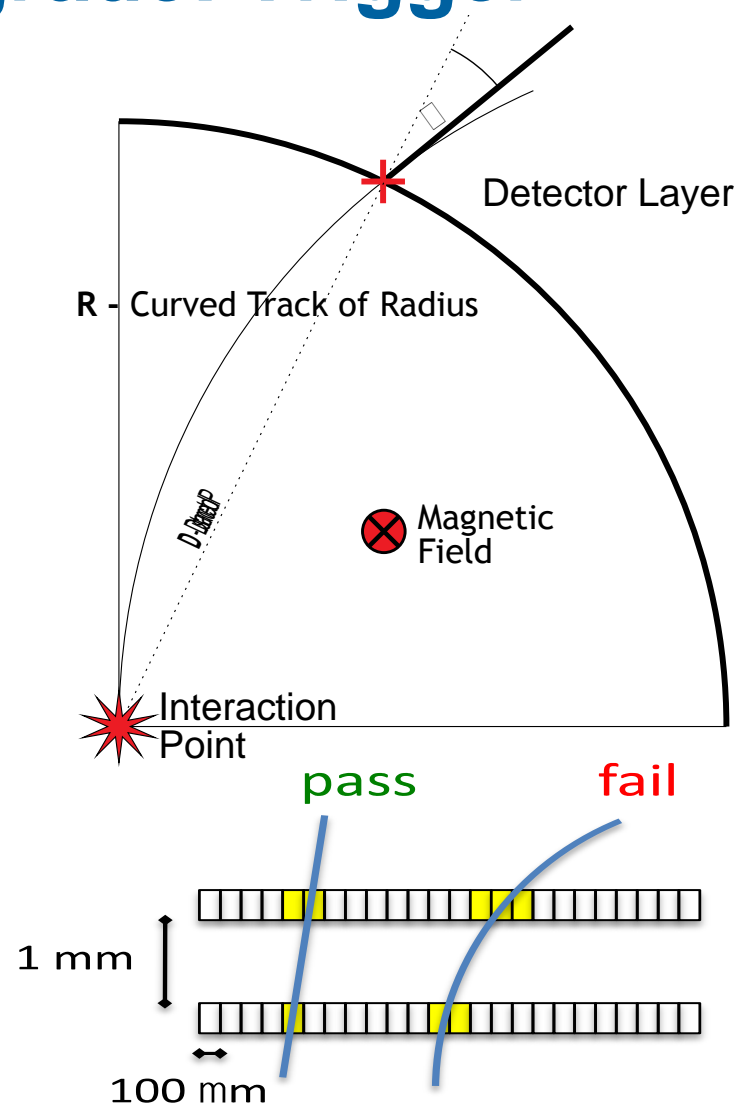


Expected fluence (10 years)

- Outermost layer (110 cm)
~ 1×10^{14} 1 MeV Neutrons/cm²
- Innermost layer (20 cm)
~ 1×10^{15} 1 MeV Neutrons/cm²

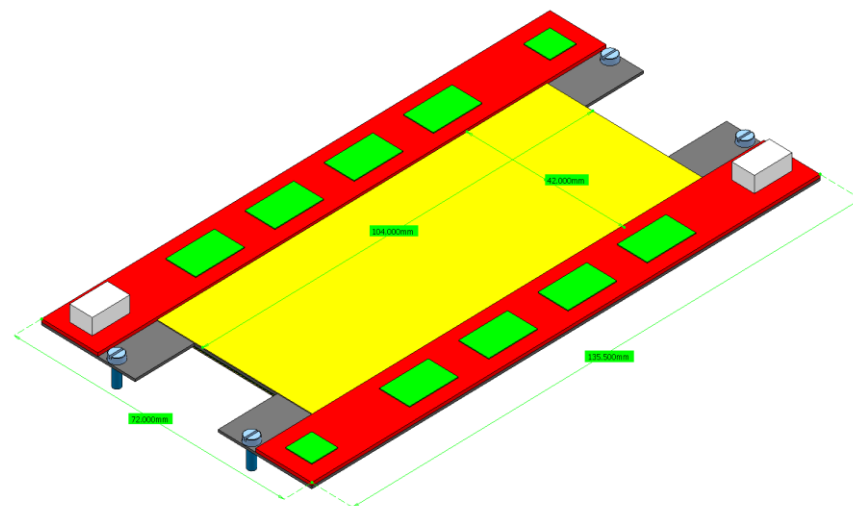
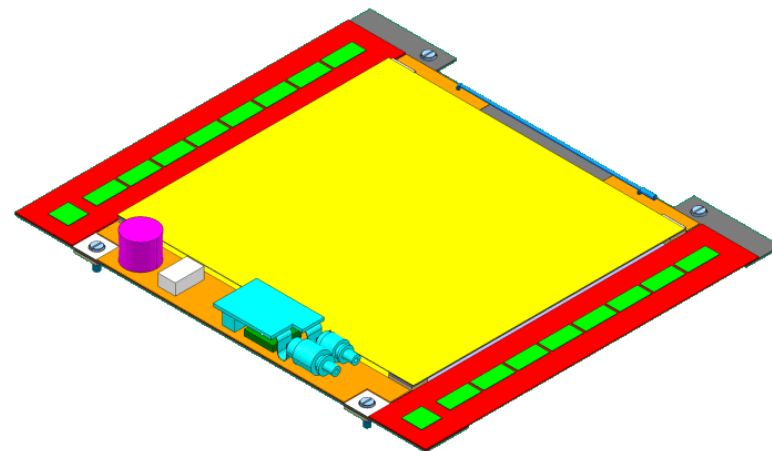
Challenges for the Upgrade: Trigger

- Cannot send full tracker information to the trigger due to bandwidth limitation
- Send hits from particles with high momentum to the trigger
- Estimate particle momentum on **module level**
 - At given magnetic field the track **curvature** depends on the **particle's p_t**
 - **Different curvature** results in **different incident angles** at a given radius
 - Estimate **incident angle** from **hit displacement** over a short distance
→ two parallel sensor planes



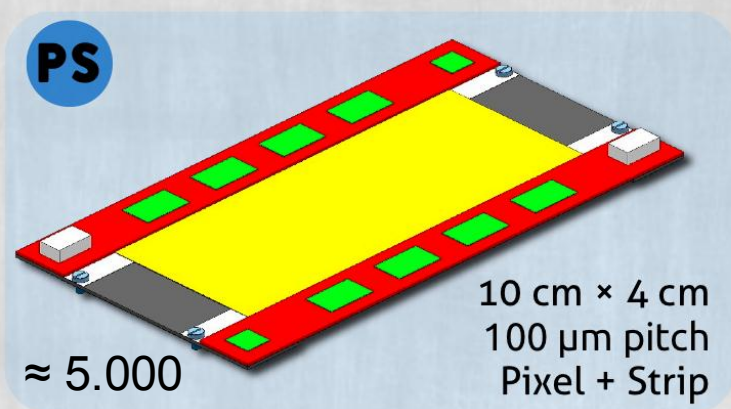
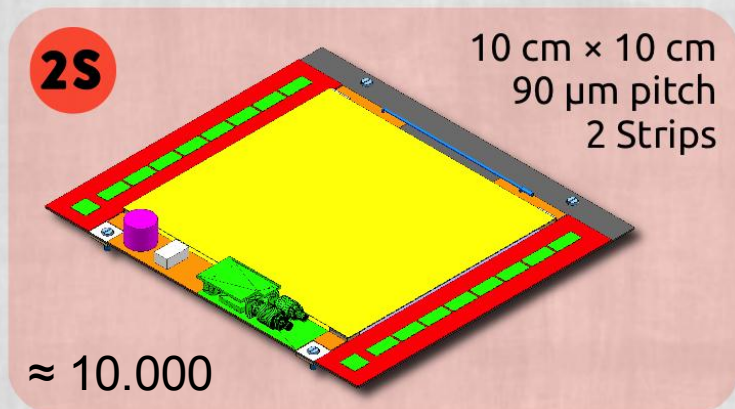
New Modules

- 2S: Module with two strip sensors
 - **2 x AC coupled strip** sensor with polysilicon biasing
 - 90 micron pitch
 - 10 x 10 cm size (6" wafers)
 - 2 x 1016 strips per sensor = 4064 Channels per module
- PS: Module with one strip and one pixel sensor
 - **1 x AC coupled strip** sensors with polysilicon biasing
 - 100 micron pitch
 - **1 x DC coupled macro-pixel** sensors with polysilicon or punch trough biasing
 - long pixels/short strips ~ 1-2 mm length
 - 10 x 4 cm size (6" wafers)
 - 32.768 pixels + 2032 strips



Barrel + End-cap layout

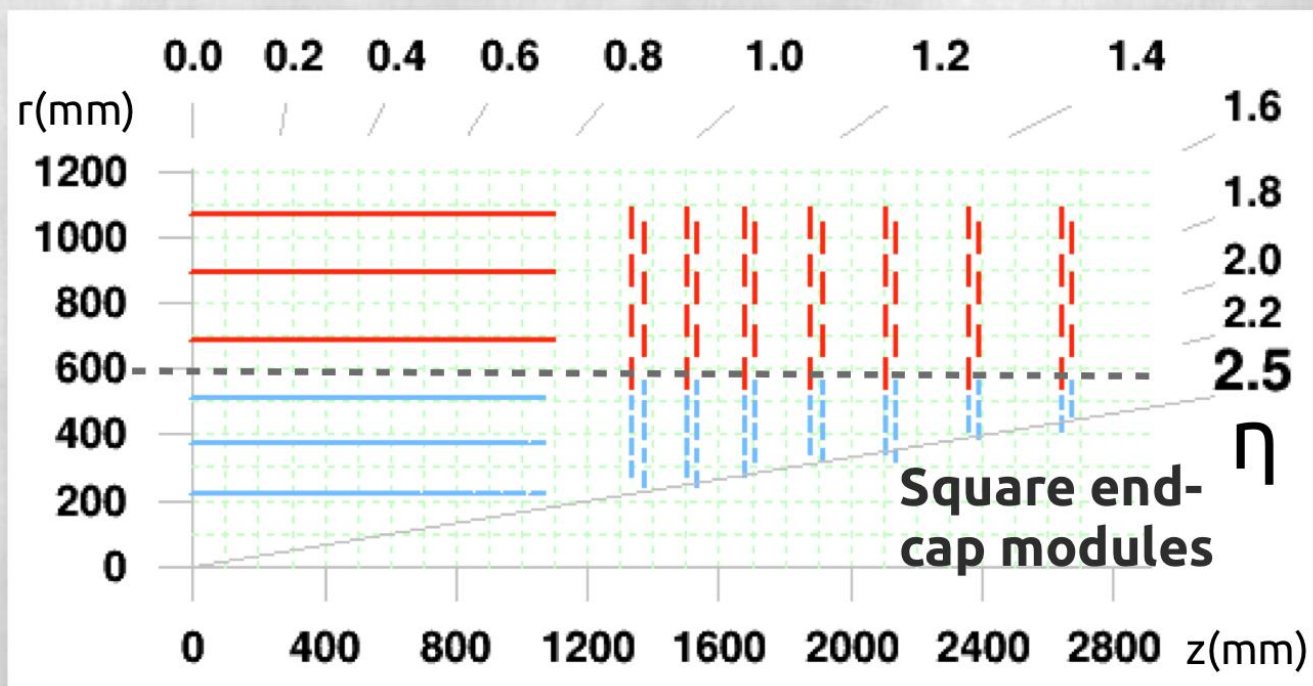
From S. Mersi,
30 January 2012



→ $\approx 240 \text{ m}^2$ of silicon

Lower density
2S modules
outside

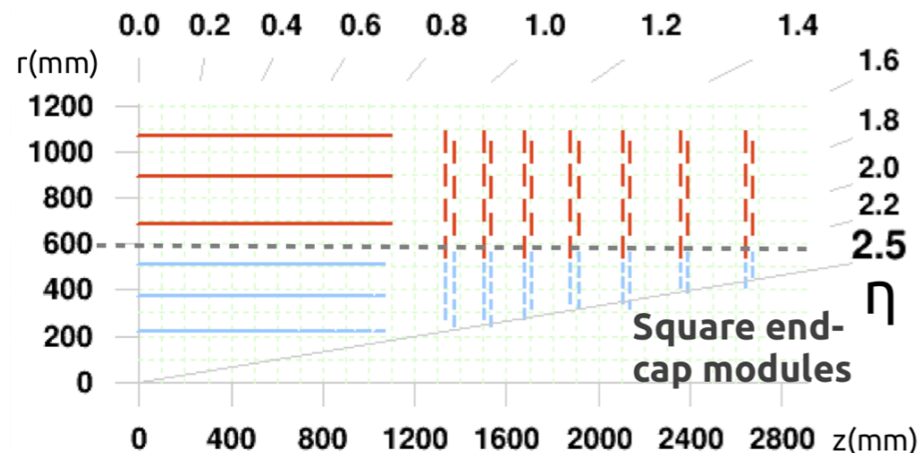
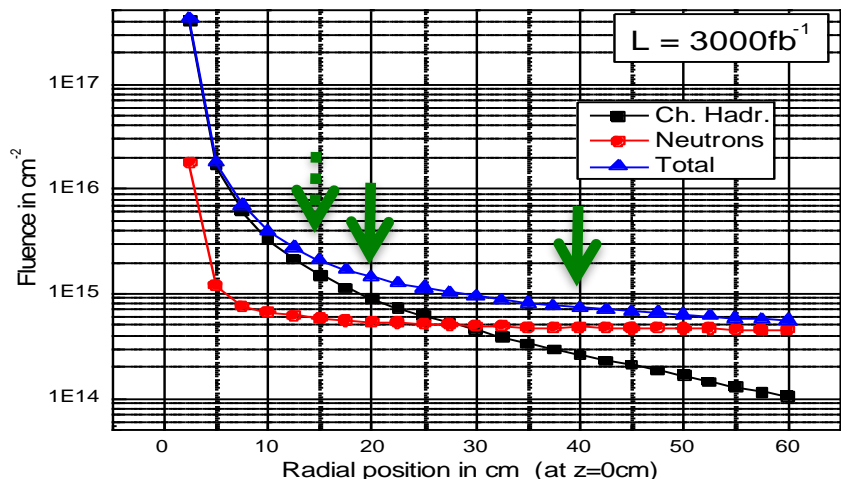
z info in trigger
 θ info in trigger
PS modules inside
2 for measurement
+1 for redundancy



NEW SENSORS

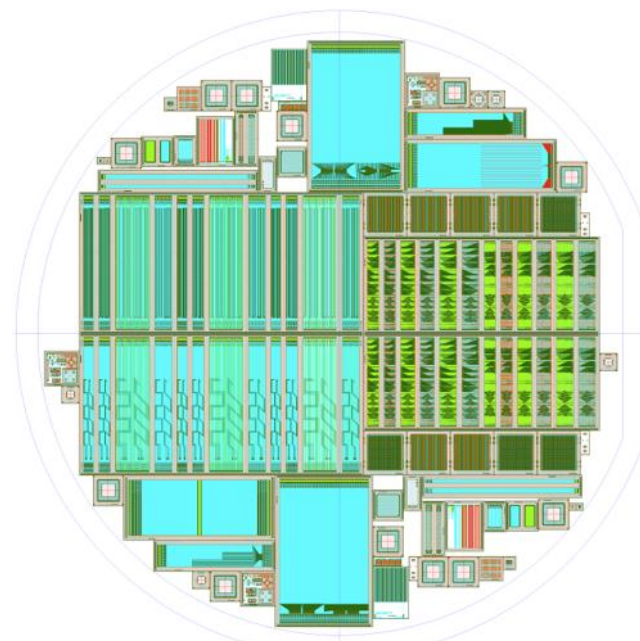
Sensors: Bulk Materials

- Different radiation tolerant bulk materials are potential candidates
 - We might use one or several materials optimised to different radii from the interaction point
 - Radiation higher towards center
 - Sensor area increases towards outside
- Cheaper „standard“ materials in outer region, more radiation tolerant materials inside



Sensors: Bulk Materials

- CMS Tracker has a large campaign on-going investigating radiation tolerant materials and production processes using test sensors and structures



	physical thickness		deep diffusion		carrier wafer		
active thickness	320μ	200μ	200μ	120μ	120μ	100μ	50μ
FZ	X	X	X	X	X		
MCz		X					
Epi						X	X

Sensors: Processing

We investigate 3 processes (on all materials):

- **p-on-n**: p-strips in n-bulk
- **n-on-p, p-stop**: n-strips in p-bulk with p-stop isolation
- **n-on-p, p-spray**: n-strips in p-bulk with p-spray isolation

We will need:

- **AC coupled strip** sensors (single-sided) with polysilicon biasing
- **DC coupled macro-pixel** sensors with polysilicon or punch through biasing

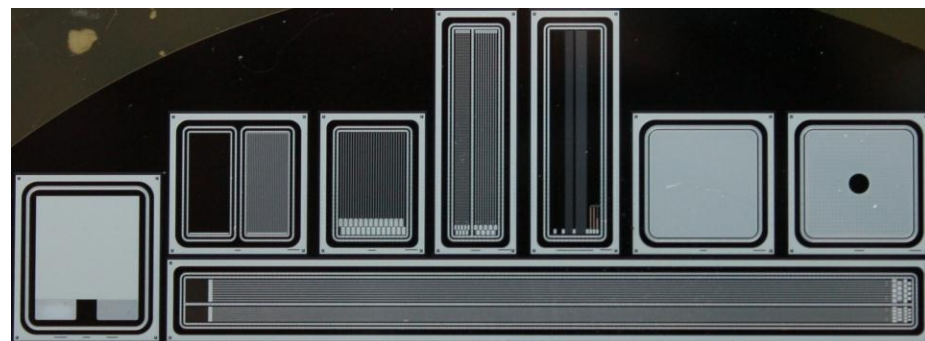
Sensors: Important Characteristics

- HV operation
 - Long-term stable operation up to 500 V
 - Even after irradiation!
- Low reverse bias current
 - $< 1 \mu\text{A}@400\text{V}@20^\circ \text{C}$ ($\sim < 1 \mu\text{A}/\text{cm}^2$)
for $10 \times 10 \text{ cm}^2$ area, $320 \mu\text{m}$ thickness
- High quality dielectric between aluminium readout strip – strip implant
 - Low count of pinholes (short between alu - implant) $< \%$ of strips
 - Breakthrough voltage of dielectric $> 150 \text{ V}$
- Stable production line
 - Changes in the production might influence the required quality and radiation hardness
 - Even small changes can have unexpected effects

Sensors: Electrical Characterisation

*Measurements on dedicated test structures
to assess the quality of production process*

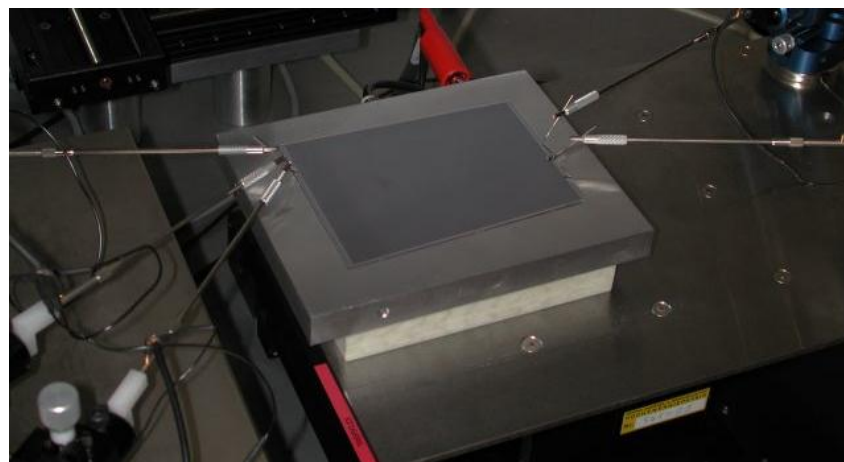
- Diode Properties
 - Full depletion voltage (V_{depl} from CV-curve)
 - Reverse bias current (I_{leak} from IV-curve)
- Strip Properties
 - Interstrip resistance: R_{int}
 - Interstrip capacitance: C_{int}
- Oxide Properties (dielectric between strip implant and readout strip)
 - Coupling capacitance (oxide thickness): C_{ox}
 - Dielectric current, breakthrough voltage: I_{diel} , V_{break}
 - Flatband voltage (MOS, GCD): V_{fb}
 - Surface current (GCD): I_{surf}
- Sheet Resistances
 - Polysilicon: R_{poly}
 - Implants: R_{strip} , R_{stop}
 - Alu: R_{alu}



Sensors: Electrical Characterisation

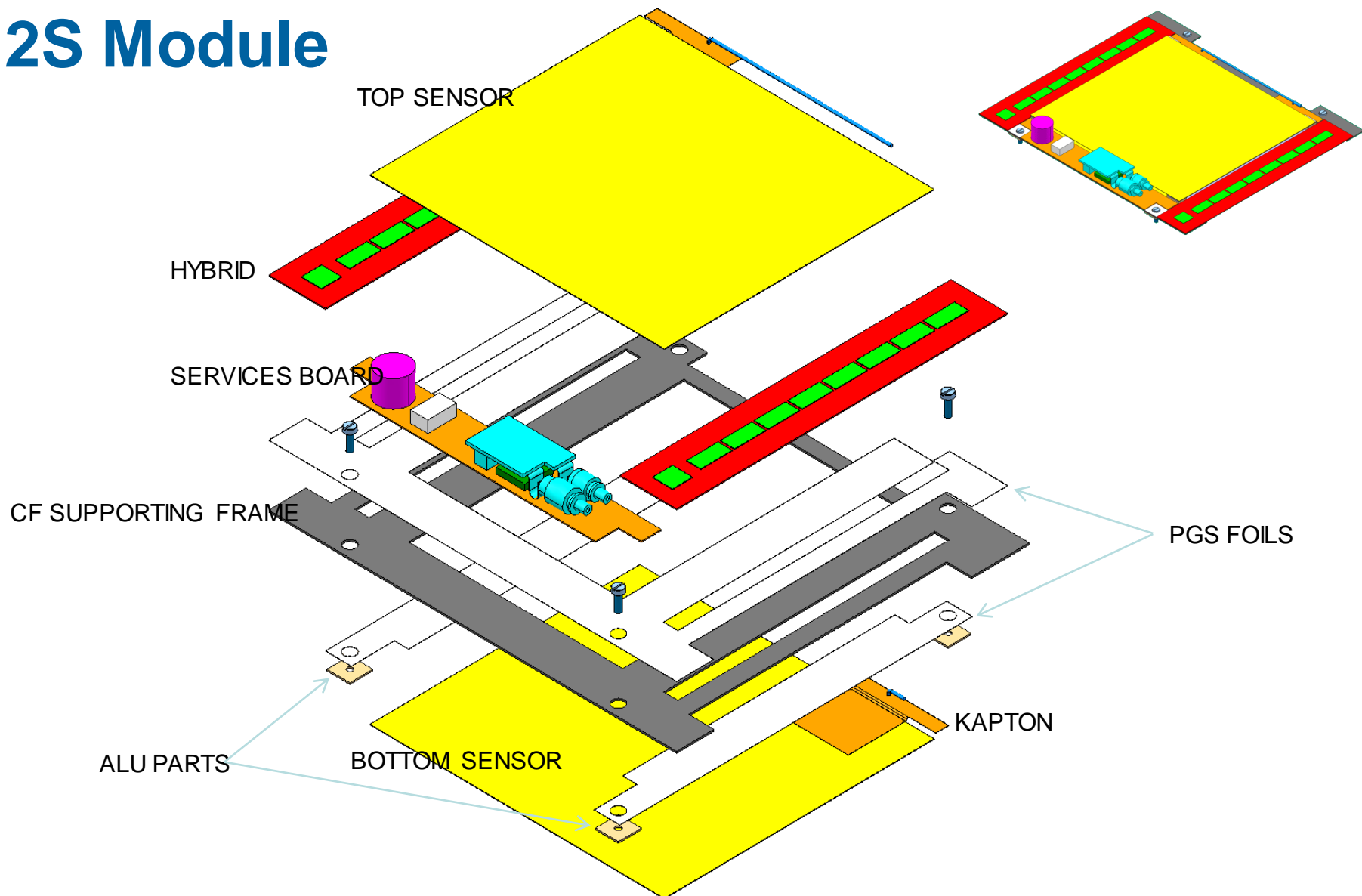
*Measurements on sensor
to assess the quality of sensors on a sample basis*

- Global Measurements
 - Full depletion voltage (V_{depl} from CV-curve)
 - Reverse bias current (I_{leak} from IV-curve)
- Strip Properties
 - Interstrip resistance: R_{int}
 - Interstrip capacitance: C_{int}
 - Coupling capacitance: C_{ox}
 - Polysilicon resistor: R_{poly}
 - Pinholes (current through dielectric)

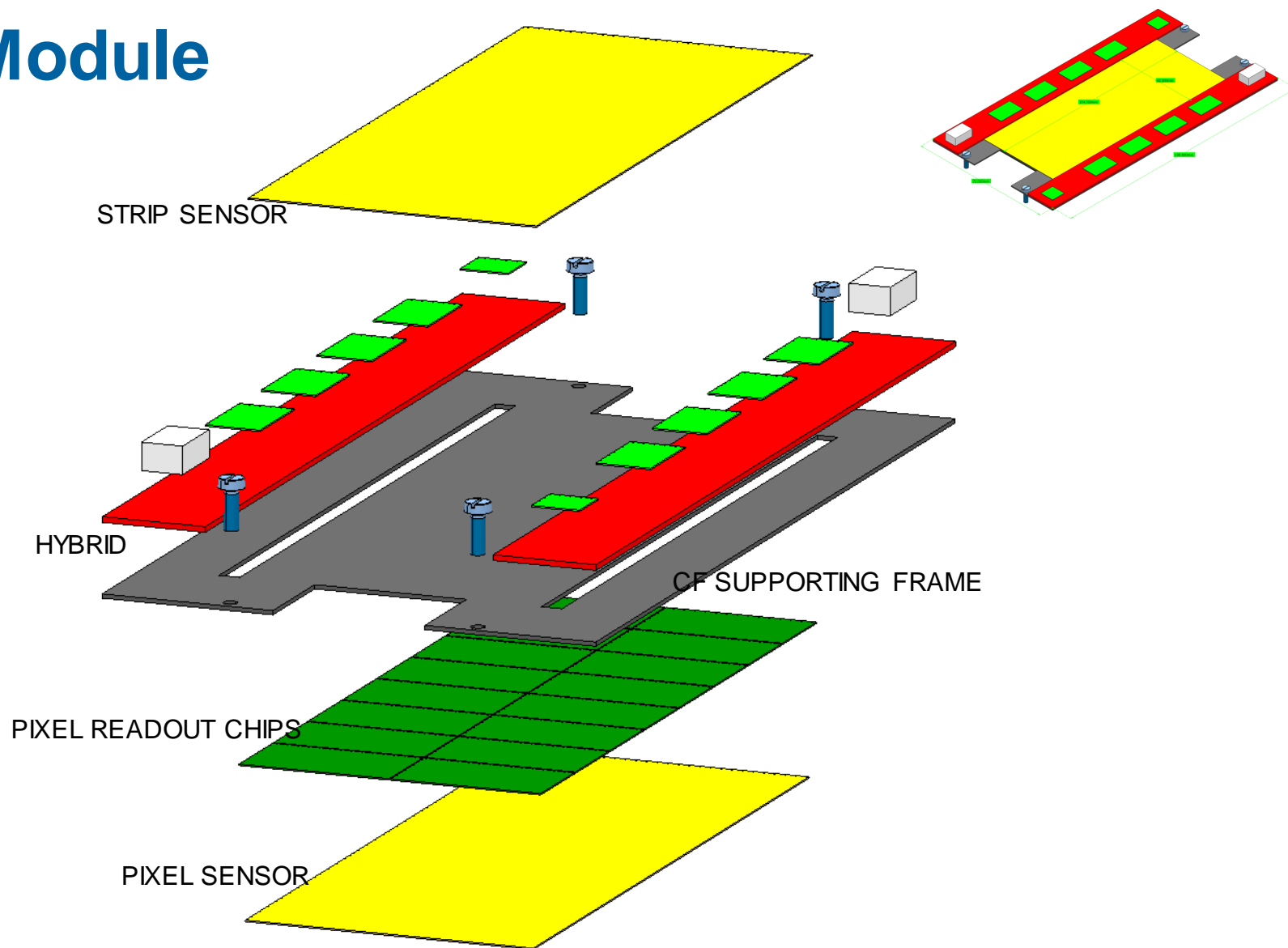


MODULE COMPONENTS

2S Module



PS Module



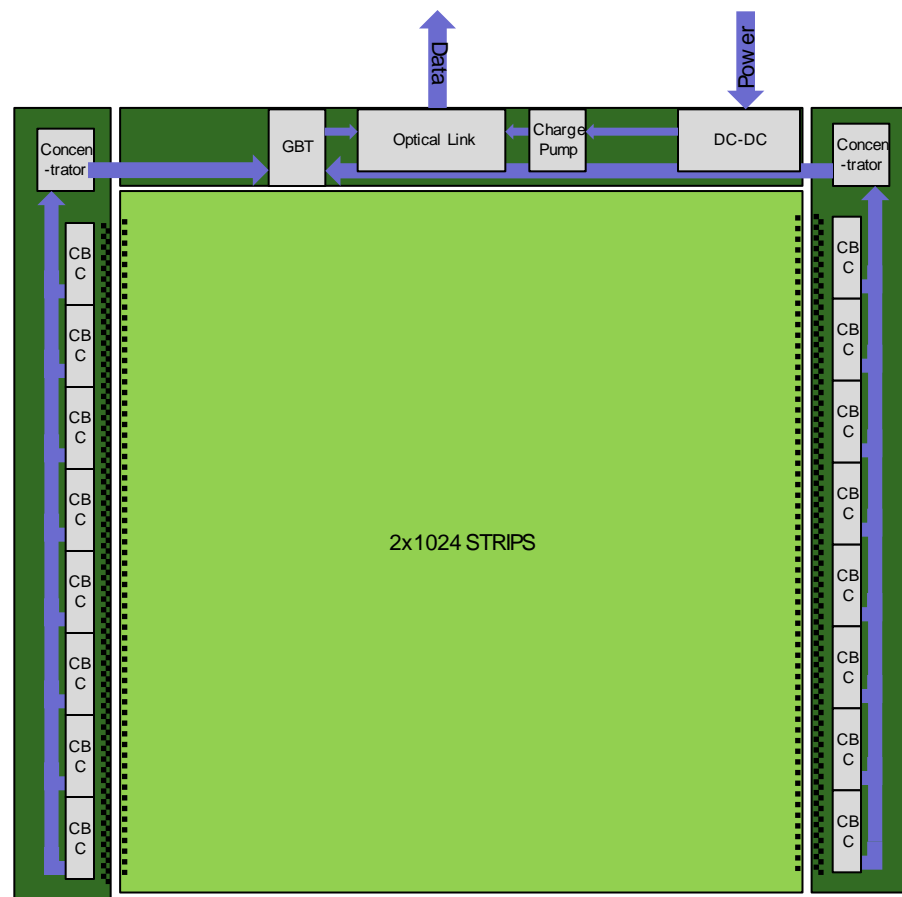
2S Modules: Electronics

Hybrid

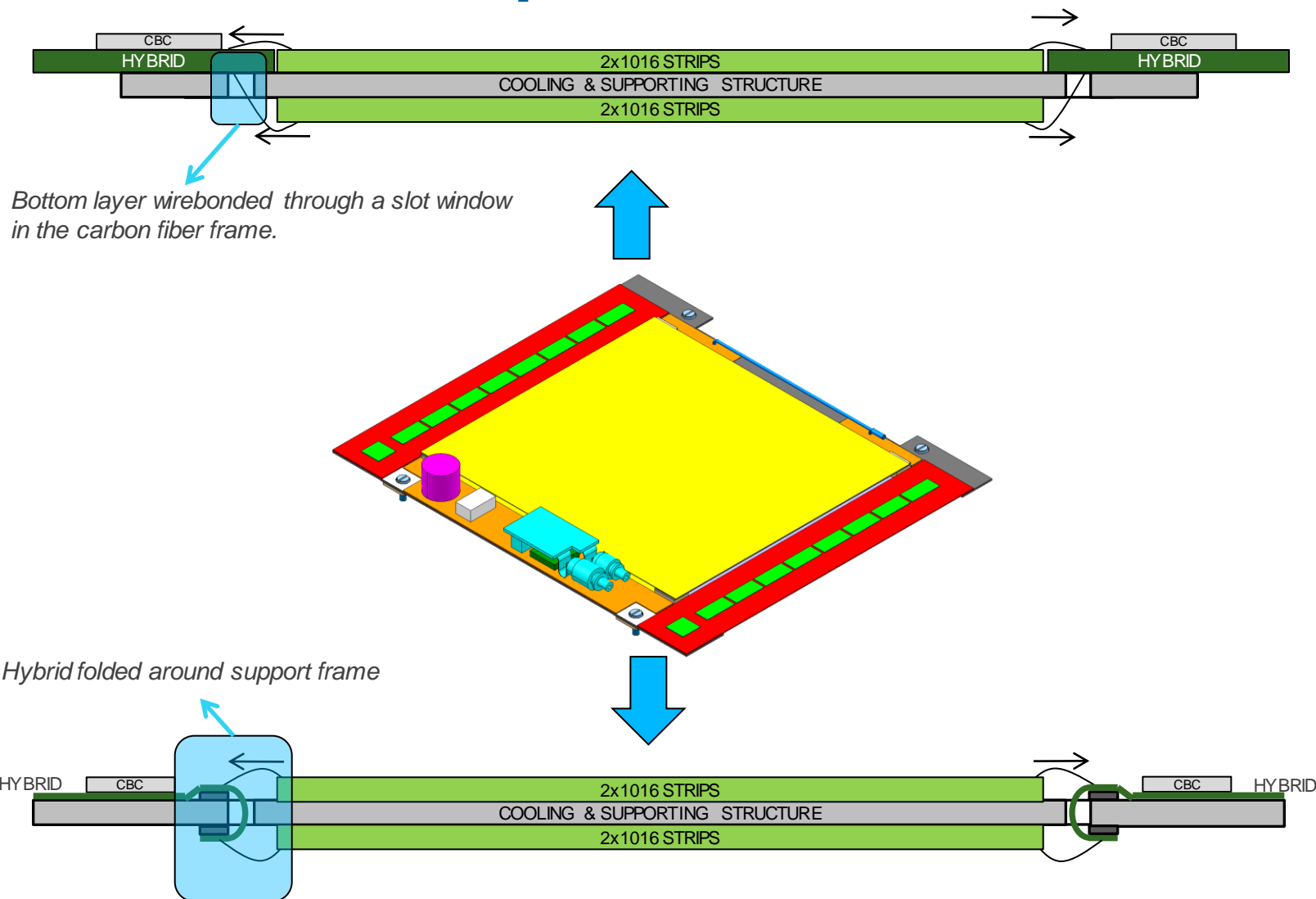
- 2 x 8 readout chips with 254 channels each
 - Chips are bump bonded to hybrid
 - Communicate with neighbour chip and concentrator chip
 - Each chip connects to strips on top and bottom sensor via wire bonding from hybrid
- Lightweight hybrid board needs multiple layers with high density interconnects and bump and wire bonding capability

Service board

- Might be an additional board or integrated with hybrid
- Houses DC-DC converter, optical link and the corresponding connectors
- Lightweight connectors for low voltage, high voltage and optical data link

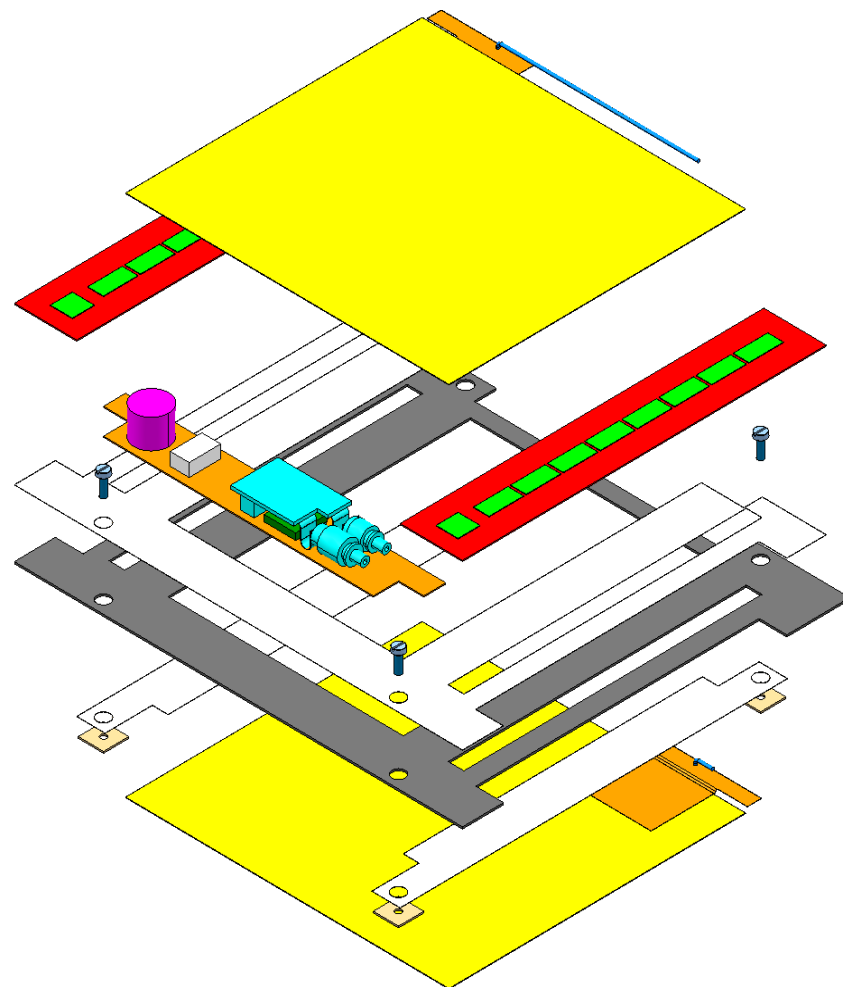


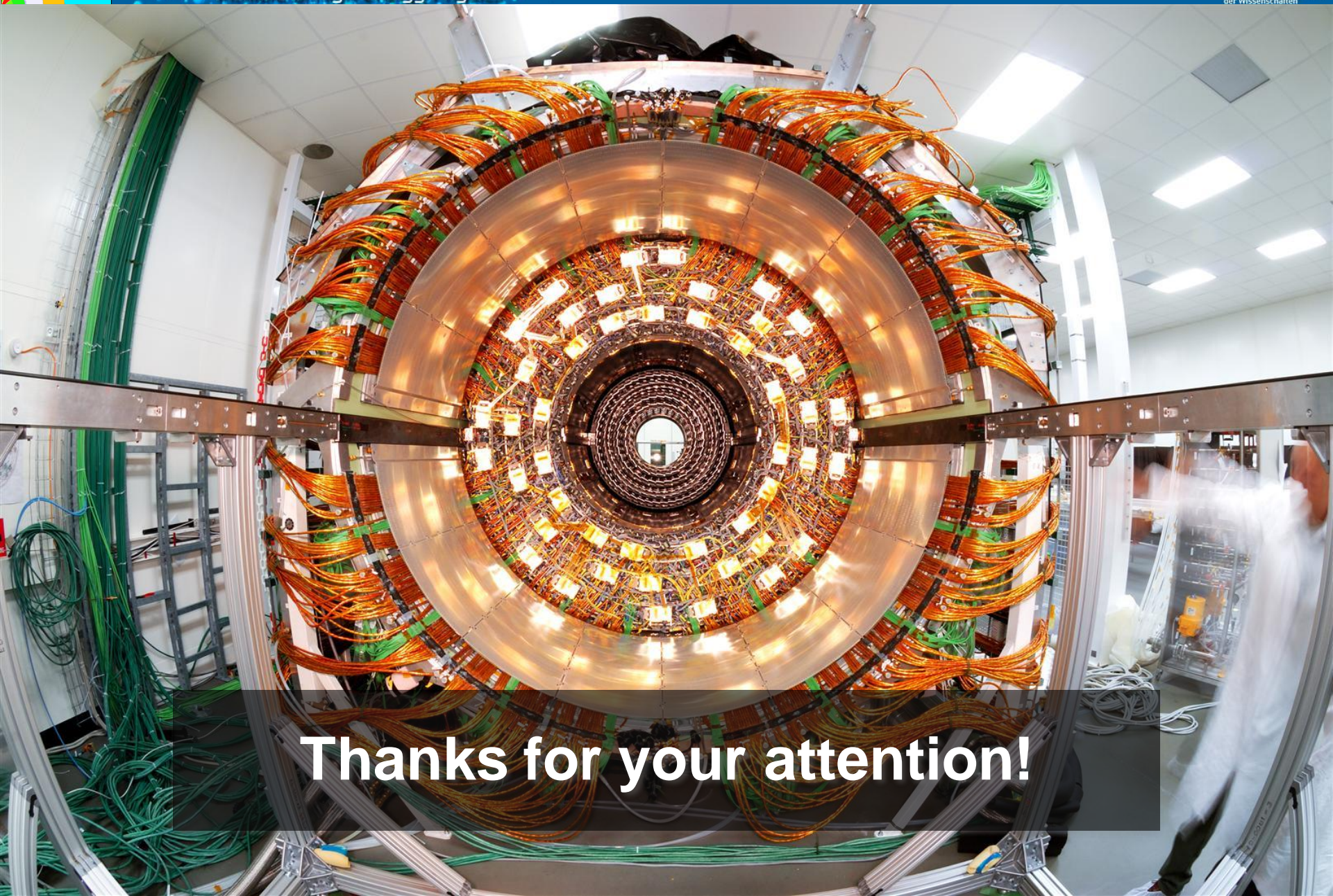
2S Modules: Chip to Sensor Connections



2S Modules: Support and Cooling

- Stiff and lightweight support materials (CFRP)
- Thin heat spreader material for thermal management
- Radiation tolerant glue with good thermal conductivity





Thanks for your attention!